JL7018F Datasheet

Zhuhai Jieli Technology Co.,LTD

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JL7018F Features

CPU

- 32bit Dual-Core DSP
- Maximum speed 160MHz
- 32KB ICache and 16KB DCache
- IEEE754 Single precision FPU
- Mathematical accelerate engine
- Interrupts with 8 priority level

Memory

- On-chip 640KB SRAM
- Support MMU
- Built-In Flash

Clocks

- On-chip 16 MHz clock oscillator
- On-chip 200 kHz lower-temperature-drift clock oscillator
- 24 MHz crystal oscillator

DSP Audio Processing

- SBC, AAC Audio decodes supported for BT audio
- mSBC voice codec supported for BT phone
- Supports MP2, MP3, WMA, APE, FLAC, AAC, MP4, M4A, WAV, AIF, AIFC audio decoding
- Packet Loss Concealment (PLC) for voice processing
- Single/Dual MIC Environmental Noise Cancellation (ENC)
- Multi-band DRC limiter
- Multi-band EQ configuration for voice Effects

Audio Codec

- Two channels 24-bit DAC, $SNR \ge 104dB$
- Four channels 24-bit ADC,SNR ≥ 95dB
- Audio DAC Sampling rates of 8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32kHz/44.1kHz/48kHz/64kHz/88.2kHz/96kHz are supported

- Audio ADC Sampling rates of 8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32 kHz/44.1kHz/48kHz are supported
- Support four digital/analog MIC inputs
- Four channels analog audio inputs
- Audio DAC supports differential cap-less mode or single-ended mode
- Direct drive 16ohm/32ohm Speaker loading

ANC

- ANC processing engine up to 750 kHz sample rate
- 7.5μs analog to analog latency
- Supports 4 differential or single-ended analog inputs, 4 digital microphone inputs for ANC
- Supports 2 channels Feed-Forward, Feed-Back, Hybrid ANC
- ANC module include 20 double precision Biquad filters for each FF/FB/ music compensation control

Bluetooth

- Compliant with Bluetooth
 V5.3+BR+EDR+BLE specification
- Support AoA/AoD direction finding
- Support LE audio BIS/CIS full function
- Meet class2 and class3 transmitting power requirement
- Maximum +9dbm transmitting power
- EDR receiver with minimum -95dBm sensitivity
- Support a2dp\avctp\avdtp\avrcp\hfp\spp\smp\
 att\gap\gatt\rfcomm\sdp\l2cap profile
- bap 1.0\pacs 1.0\ccp 1.0\mcp 1.0\micp 1.0\vcp 1.0\csip 1.0
- a2dp 1.3.2\avctp 1.4\avdtp 1.3\ avrcp
 1.6.2\hfp 1.8 \spp 1.2\rfcomm 1.1\pnp 1.3\hid
 1.1.1\sdp core5.3\l2cap core 5.3



Peripherals

- One full speed USB OTG controller
- One SD host controller for eMMC/SD
- Six multi-function 32-bit timers, support capture and PWM mode
- Four UART interface, UART0,UART1&UART2 support DMA
- I2C Master/Slave interface
- SPI Master/Slave interface
- I2S Master/Slave interface
- QDEC
- Low power CapSense
- 12-channel 10-bit ADC for analog sampling
- 4-channel Motor PWM controller
- 24 Individually programmable and multiplexed GPIO pins
- Up to 12 external interrupt/wake-up source(low power available,can be multiplexed to any I/O)

PMU

- Built-in lithium battery charging manager,up to 200mA charging current
- Built-in LDO and Buck DC-DC converter
- Less than 2uA sleep current
- VPWR range : 4.5V to 5.5V
- VBAT range : 2.2V to 4.5V
- IOVDD range: 2.2V to 3.6V

Packages

QFN40(5mm*5mm)

Temperature

- Operating temperature: -40°C to +85°C
- Storage temperature: -65°C to +150°C

Applications

- Bluetooth Stereo Headsets and Headphones
- Bluetooth Stereo ANC Headsets and Headphones
- Bluetooth TWS ANC Earphones





1 Block Diagram

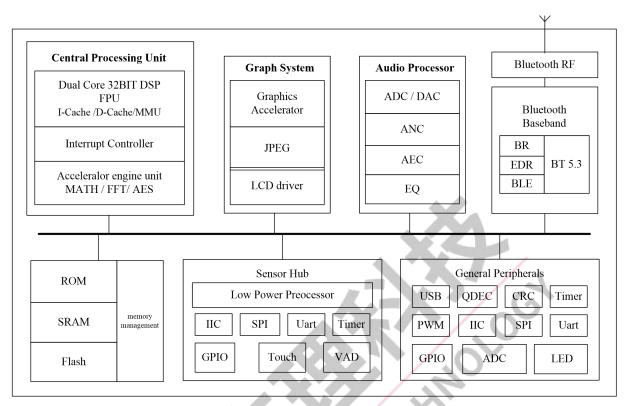


Figure 1-1 JL7018F Block Diagram



2 Pin Definition

2.1 Pin Assignment

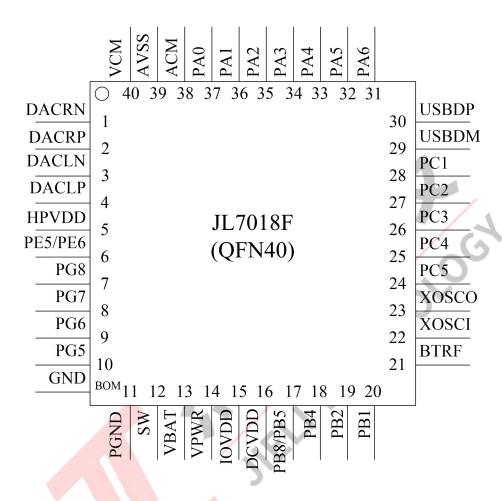


Figure 2-1 JL7018F Package Diagram



2.2 Pin Description

Table 2-1 JL7018F Pin Description

PIN NO.	Name	Туре	Function	Other Function		
1	DACRN	AO		Different DAC Right Negative Channel		
2	DACRP	AO		Different DAC Right Positive Channel		
3	DACLN	AO		Different DAC Left Negative Channel		
4	DACLP	AO		Different DAC Left Positive Channel		
5	HPVDD	PI		Audio power		
	PE6	I/O	GPIO	SDPG: supply voltage to SD Card		
6	PE5	I/O	GPIO	SPI4_D3(PSRAM): SPI4 Data3; SPI0_DAT3D: SPI0 Data3(D);		
7	PG8	I/O	GPIO	MICIN2: MIC2 Input Channel 2; MIC2_P: Different MIC2 Positive; AMUX_C0:Analog Channel C0 input;		
8	PG7	I/O	GPIO	MIC_BIAS2: MIC2 Bias Output(Built-in resistor); MIC2_N: Different MIC2 Negative; AMUX_C1: Analog Channel C1 input; ADC15: ADC Input Channel 15;		
9	PG6	I/O	GPIO	MICIN3: MIC3 Input Channel3; MIC3_P: Different MIC3 Positive; AMUX_D0: Analog Channel D0 input; FPIN2: Fault Detect In2;		
10	PG5	I/O	GPIO	MIC_BIAS3: MIC3 Bias Output(Built-in resistor); MIC3_N: Different MIC3 Negative; AMUX_D1:Analog Channel D1 input; ADC14: ADC Input Channel 14; TMR3CK: PWM Timer3 CLK In;		
11	PGND	G		The ground of Buck DC-DC converter;		
12	SW	PO	1	Switch signal of the Buck converter, connected to Inductor;		
13	VBAT	P		Power Supply, connect to battery;		
14	VPWR (PP0)	PI (I/O)	GPIO (High Voltage Resistant)	Charging Power Input; UART0TXB: Uart0 Data Out(B); UART0RXB: Uart0 Data In(B); PWM3: Timer3 PWM Output; CAP1: Timer1 Capture;		
15	IOVDD	PO		Built-in linear voltage regulator output;		
16	DCVDD	P		Internal Power;		



				EVDD: Supply voltage 1.1V;		
	PB8	I/O	GPIO	CAP4: Timer4 Capture;		
				LP Touch4: Low Power Touch Channel 4;		
17				IIC1_SDA_A: IIC1 SDA(A);		
	PB5	I/O	GPIO	ADC8: ADC Input Channel 8;		
				UART3RXB: Uart3 Data In(B);		
				LP Touch3: Low Power Touch Channel 3;		
				CLKOUT0: CLK Output Channel 0;		
				SPI4DIA: SPI4 Data In(A);		
18	PB4	I/O	GPIO	IIC1_SCL_A: IIC1 SCL(A);		
				UART3TXB: Uart3 Data Out(B);		
				TMR2: Timer2 Clock Input;		
				LP_Touch2: Low Power Touch Channel 2;		
				SPI4CLKA: SPI4 Clock(A);		
10	22.0	7/0	anv.	Q-decoder0_0: Quadrature decoder0_0;		
19	PB2	I/O	GPIO	ADC7: ADC Input Channel 7;		
				UART3TXA: Uart3 Data Out(A);		
				CAP5: Timer5 Capture;		
				Hold down 0 to reset;		
20	PB1	I/O	GPIO	LP_Touch1: Low Power Touch Channel 1;		
				ADC6: ADC Input Channel 6;		
21	BTRF	RFI		Bluetooth RF antenna interface;		
22	XOSCI	I		System Crystal Oscillator Input;		
23	XOSCO	0		System Crystal Oscillator Output;		
				SPI0_DAT2C: SPI0 Data2(C);		
				SD0_CLKA: SD0 Clock(A);		
		A Briston		SPI1DOB: SPI1 Data Out(B);		
24	PC5	I/O	GPIO	IIC0_SDA_B: IIC0 SDA(B);		
		1		ALNK_DAT3(B): Audio Link Data3(B);		
		A. Carrier		ADC5: ADC Input Channel 5;		
				UART2RXA: Uart2 Data In(A);		
		A		SPI0_DIC: SPI0 Data In(C);		
		A Committee of the Comm		SD0CMDA: SD0 CMD(A);		
		and a		SPI1CLKB: SPI1 Clock(B);		
25	DC4	I/O	CDIO	IIC0_SCL_B: IIC0 SCL(B);		
25	PC4	I/O	GPIO	ALNK_DAT2B: Audio Link Data2(B);		
				ADC4: ADC Input Channel 4;		
				UART2TXA: Uart2 Data Out(A);		
				PWM4: Timer4 PWM Output;		



			I			
26	PC3	I/O	GPIO	SPI0_CSC: SPI0 Chip Select(C); SD0DATOA: SD0 Data Out(A); SPI1DIB: SPI1 Data In(B); ALNK_LRCKB: Audio Link Word Select(B); TMR3: Timer3 Clock Input;		
27	PC2	I/O	GPIO	SPI0_DOC: SPI0 Data Out(C); ALNK_SCLKB: Audio Link Serial Clock(B);		
				TMR1: Timer1 Clock Input;		
				SPI0_CLKC: SPI0 Clock(C);		
28	PC1	I/O	GPIO	ALNK_DAT1B: Audio Link Data1(B);		
	101	1,0	5115	TMR5: Timer5 Clock Input;		
				PWMCH1L: PWM CH1 Low;		
				SDTAP_DATB: SDTAP Data(B);		
			USB Negative Data	SPI2DOB: SPI2 Data Out(B);		
29	USBDM	I/O	(pull down)	IIC0_SDA_A: IIC0 SDA(A);		
			(4)	ADC11: ADC Input Channel 11;		
				UART1RXB: Uart1 Data In(B);		
				SDTAP_CLKB: SDTAP CLK(B);		
		I/O	USB Positive Data (pull down)	SPI2CLKB: SPI2 Clock(B);		
30	USBDP			IIC0_SCL_A: IIC0 SCL(A);		
			(4)	ADC10: ADC Input Channel 10;		
				UART1TXB: Uart1 Data Out(B);		
				PLNK_DAT0: PLNK Data 0;		
				SPI2DOA: SPI2 Data Out(A);		
31	PA6	I/O	GPIO	ALNK_DAT3A: Audio Link Data3(A);		
				ADC2: ADC Input Channel 2;		
		The same		UART0RXA: Uart0 Data In(A);		
				CAP0: Timer0 Capture;		
				PLNK_SCLK: PLNK Serial Clock;		
				SPI2CLKA: SPI2 Clock(A);		
32	PA5	I/O	GPIO	ALNK_DAT2A: Audio Link Data2(A);		
				ADC1: ADC Input Channel 1;		
				UART0TXA: Uart0 Data Out(A);		
		No. of		MIC_BIAS1: MIC1 Bias Output(Built-in resistor);		
				MIC1_N: Different MIC1 Negative;		
33	PA4	I/O	GPIO	AMUX_B1:Analog Channel B1 input;		
			0.10	SPI2DIA: SPI2 Data In(A);		
				ALNK_DAT1A: Audio Link Data1(A);		
				CAP2: Timer2 Capture;		



				MICIN1: MIC1 Input Channel 1;
				MIC1_P: Different MIC1 Positive;
34	PA3	I/O	GPIO	AMUX_B0:Analog Channel B0 input;
34	PAS	1/0	GPIO	SPI1DOA: SPI1 Data Out(A);
				ALNK_DAT0(A): Audio Link Data0(A);
				PWM1: Timer1 PWM Output;
				MIC_BIAS0: MIC0 Bias Output(Built-in resistor);
				MIC0_N: Different MIC0 Negative;
				AMUX_A1:Analog Channel A1 input;
35	PA2	I/O	GPIO	CLKOUT1: Clock Out1;
33	PAZ	1/0	GPIO	SPI1CLKA: SPI1 Clock(A);
				ALNK_MCLKA: ALNK Master Clock(A);
				UART1RXA: Uart1 Data In(A);
				CAP3: Timer3 Capture;
				MICIN0: MIC0 Input Channel 0;
				MIC0_P: Different MIC0 Positive;
36	PA1	I/O	GPIO	AMUX_A0:Analog Channel A0 input;
30	IAI	1/0	GI IO	SPI1DIA: SPI1 Data In(A);
				UART1TXA: Uart1 Data Out(A);
				PWM0: Timer0 PWM Output;
37	PA0	I/O	GPIO	MICLDO: MIC Power Supply;
37	PAU	1/0	GPIO	ADC0: ADC Input Channel 0;
38	ACM	P		Audio analog reference bias;
39	AVSS	P		Audio analog ground;
40	VCM	G		Audio ADC/DAC reference;
PAD	VSS	G		System Ground;

Pin Type	Description	Pin Type	Description
P	Power	I/O	Input or Output
PO	Power Output	I	Input
PI	Power Input	0	Output
G	Ground	RFI	Radio frequency interface
AO	Analog Output		



3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-40	+85	°C
Tstg	Storage temperature	-65	+150	°C
VBAT	Supply Voltage	-0.3	4.5	V
VPWR	Charger Voltage	-0.3	6	V
V _{IOVDD}	Voltage applied at IOVDD	-0.3	3.6	V
V_{GPIO}	Voltage applied to GPIO	-0.3	IOVDD+0.3	V
V _{HVIO}	Voltage applied to High Voltage Resistant IO	-0.3	+5.5	V
V _{HPVDD}	Voltage applied at HPVDD	-0.3	+3	V

Note: The chip can be damaged by any stress in excess of the absolute maximum ratings listed below

3.2 PMU Characteristics

Table 3-2

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
VBAT	Voltage Input	2.2	3.7	4.4	V	
VPWR	Charger supply Voltage	4.5	5.0	5.5	V	.0
Operating mod	le					
IOVDD	Voltage output	_	3.0	/_/	V	VBAT = 4.2V, 10mA loading
ממיסו	Loading current	_	/	200	mA	IOVDD=3.2V@VBAT = 3.5V
	Voltage output	_	1.25		V	IOVDD=3.0V, 10mA loading
DCVDD	Loading current	1	_	100	mA	DCVDD=1.25V@IOVDD=3.0v on LDO mode
			-	180	mA	DCVDD=1.25V@VBAT=3.0v on DCDC mode
EVDD	Voltage output	7 _	1.1	_	V	DCVDD=1.25V, 1mA loading
EVDD	Loading current	_	_	5	mA	EVDD=1.1V@DCVDD=1.25v
Low Power mo	ode					
IOVDD	Loading current	_	_	10	mA	IOVDD=3V@VBAT = 4.2V



3.3 Battery Charge

Table 3-3

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
VPWR	Charge Input Voltage	4.5	5	5.5	V	-
V _{bat float}	Charge Voltage	4.15	4.2	4.25	V	VPWR>4.5V
V bat float	Charge Voltage	4.30	4.35	4.40	V	VPWR>4.65V
I _{bat}	Charge Current	15	ı	200	mA	Charge current at fast charge mode VBAT=4.0V@VPWR=5.0V
$ m I_{end}$	End Of Charge Current	2	I	30	mA	End of charge current
V_{Trikl}	Trickle Charge Voltage	_	3.0	_	v	VPWR>4.5V
${ m I}_{ m Trikl}$	Trickle Charge Current	1.5	_	30	mA	$V_{BAT} \!\!<\! V_{Trikl}$

3.4 IO Input/Output Electrical Logical Characteristics

Table 3-4

GPIO input	characteristics	4							
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions			
V_{IL}	Low-Level Input Voltage	-0.3	/ <u>,</u>	0.3* IOVDD	V	IOVDD = 3.0V			
$ m V_{IH}$	High-Level Input Voltage	0.7* IOVDD		IOVDD+0.3	V	IOVDD = 3.0V			
High Voltage	High Voltage Resistant IO input characteristics								
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions			
V_{IL}	Low-Level Input Voltage	-0.3	_	0.3* IOVDD	V	IOVDD = 3.0V			
$ m V_{IH}$	High-Level Input Voltage	0.7* IOVDD	_	+5V	V	IOVDD = 3.0V			
GPIO & Hig	GPIO & High Voltage Resistant IO output characteristics								
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions			
V_{OL}	Low-Level Output Voltage	_		0.1* IOVDD	V	IOVDD = 3.0V			
V_{OH}	High-Level Output Voltage	0.9* IOVDD	_	_	V	IOVDD = 3.0V			



3.5 Internal Resistor Characteristics

Table 3-5

Port	Drive(mA)		Internal Pull-Up Resistor	Internal Pull-Down Resistor	Comment
PA0~PA6	HD,HD0==0,0	2.4			
PC1~PC5	HD,HD0==0,1	8	10K	10K	
PG5~PG8	HD,HD0==1,0	26	10K	10K	1、PB1 default pull up
PE5, PE6	HD,HD0==1,1	46			2、USBDM & USBDP default pull
PP0	8		10K	10K	Down
PB1~PB8	8		10K	10K	3、internal pull-up / pull-down
USBDP	4		1.5K	15K	resistance accuracy ±20%
USBDM	4		180K	15K	

3.6 DAC Characteristics

Table 3-6

Parameter	Min	Тур	Max	Unit	Audio Format	Test Conditions
Frequency Response	20	-	20k	Hz	_	D'CC (' 1M 1
Output Swing	4	1	94_ /	Vrms	_	Differential Mode
THE		-77		dB	PCM	1KHz/0dB
THD+N	_	-70		dB	SBC	32 ohm loading
C/NI	_ 4	105	_	dB	PCM	With A-Weighted Filter
S/N	_	105		dB	SBC	rmer
Crosstalk	_	-110		dB		1KHZ/0dB
Crosstaik		-110	_	ав	_	10k ohm loading
	A. C.	_				Differential Mode
		104		dB	PCM	1KHz/-60dB
Dynamic Range			_			32 ohm loading
						With A-Weighted
	_	104	_	dB	SBC	Filter
Noise Floor	_	5.6	_	uVrms	_	A-Weighted Filter
DAC Outsid Bassas		22				Differential Mode
DAC Output Power	_	32	_	mW	_	32ohm loading



3.7 ADC Characteristics

Table 3-7

Parameter	Min	Тур	Max	Unit	Test Conditions
D		0.4		dB	Fsample=44.1kHz,Gain=0dB
Dynamic Range		94			Fin=1KHz 590mVrms
SNR	_	95	_	dB	Fsample=44.1kHz,Gain=0dB
THD+N	_	-75	_	dB	Fin=1KHz 590mVrms
SNR	_	76	_	dB	Fsample=44.1kHz,Gain=18dB
THD+N	_	-73	_	dB	Fin=1KHz 75mVrms

3.8 BT Characteristics

3.8.1 Transmitter

Basic Data Rate

Table 3-8

Parameter		Min	Тур	Max	Unit	Test Conditions
RF Transmit	Power		7	9	dBm	0
RF Power Control Range			18		dB	25°0
20dB Bandwidth			950		KHz	25°C,
In-band spurious	$F=F_0\pm 1MHz$		-20		dBm	Power Supply VBAT=3.7V
Emissions	$F=F_0\pm 2MHz$		-51	20	dBm	2441MHz
(BQB Test Mode	$F=F_0\pm 3MHz$		-55		dBm	211111112
RF_Tx Power=5dBm)	F=F ₀ +/->3MHz	1	-55	,	dBm	

Enhanced Data Rate

Table 3-9

Parameter		Min	Тур	Max	Unit	Test Conditions
Relative Power			-2		dB	
~ // DODGV	DEVM RMS		9		%	25°0
π /4 DQPSK	DEVM 99%		23		%	25°C,
Modulation Accuracy	DEVM Peak		18		%	Power Supply VBAT=3.7V
In-band spurious	$F=F_0\pm 1MHz$		-4		dBm	2441MHz
Emissions	F=F ₀ ±2MHz		-34		dBm	
(BQB Test Mode	F=F ₀ ±3MHz		-43		dBm	
RF_Tx Power=5dBm)	F=F ₀ +/->3MHz		-48		dBm	



3.8.2 Receiver

Basic Data Rate

Table 3-10

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivit	у		-92		dBm	
Co-channel Interferen	nce Rejection		10		dB	25℃,
	+1MHz		-4		dB	Power Supply
	-1MHz		-3		dB	VBAT=3.7V
Adjacent channel	+2MHz		-39		dB	2441MHz
selectivity C/I	-2MHz		-33		dB	DH5
	+3MHz		-45		dB	
	-3MHz		-28		dB	

Enhanced Data Rate

Table 3-11

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivity	У	-95	-94		dBm	9
Co-channel Interferen	ce Rejection		10		dB	25℃,
	+1MHz		-8		dB	Power Supply
	-1MHz		-8		dB	VBAT=3.7V
Adjacent channel	+2MHz		-40		dB	2441MHz
selectivity C/I	-2MHz	10	-33		dB	2DH5
	+3MHz		-45		dB	
	-3MHz		-27		dB	

3.8.3 BLE

1M Data Rate

Table 3-12

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivit	Sensitivity		-96		dBm	
RF Transmit I	Power		7		dBm	
In-band Spurious	M-N =2MHz		-37		dBm	
Emission	M-N ≥3MHz			-34	dBm	25°C
	Δfl avg		250		KHz	Power Supply
Modulation Characteristics	Δf2 99%		211		KHz	VBAT=3.7V
Characteristics	Δflavg/Δf2avg		0.9			2440MHz
Carrier Frequency Offset		-15		+15	KHz	
Frequency Drift		-25		+25	KHz	
Frequency Dri	ft Rate	-5		+5	KHz/50us	



2M Data Rate

Table 3-13

Paramete	er	Min	Тур	Max	Unit	Test Conditions
Sensitivit	Sensitivity		-94		dBm	
RF Transmit I	Power		7		dBm	
	M-N =4MHz		-44		dBm	
In-band Spurious Emission	M-N =5MHz		-43		dBm	
Linission	M-N ≥6MHz			-48	dBm	25°C
	Δf1 avg		500		KHz	Power Supply
Modulation Characteristics	Δf2 99%		428		KHz	VBAT=3.7V 2440MHz
Characteristics	Δflavg/Δf2avg		0.9			2440WITIZ
Carrier Frequency Offset		-20		+20	KHz	
Frequency Drift		-25		+25	KHz	
Frequency Drift Rate		-5	100	+5	KHz/50us	1

Long Range

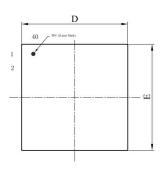
Table 3-14

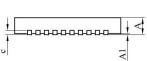
Parameter	Min	Тур	Max	Unit	Test Conditions
Sensitivity LE 125K(S8)		-104		dBm	VBAT=3.7V,25°C
Sensitivity LE 500K(S2)		-100	/ ~	dBm	2440MHz

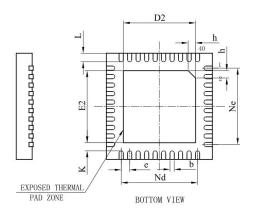


4 Package Information

4.1 QFN40_5.0x5.0







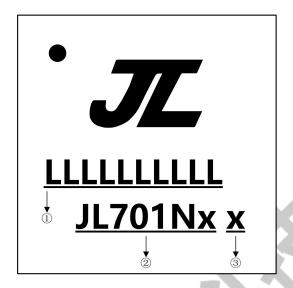
SYMBOL	MILLIMETER					
SIMBOL	MIN	NOM	MAX			
A	0.70	0.75	0.80			
A1		0.02	0.05			
b	0.15	0. 20	0. 25			
С	0.18	0. 20	0. 25			
D	4. 90	5.00	5. 10			
D2	3. 30	3. 40	3. 50			
е	0. 40BSC					
Nd	3	60BSC				
Е	4. 90	5.00	5. 10			
E2	3. 30	3. 40	3. 50			
Ne	3	. 60BSC				
L	0.35	0.40	0.45			
K	0. 20		1			
h	0.30	0.35	0.40			
L/F载体尺寸 (mil)	150*150					

Figure 4-1 JL7018F Package





5 IC Marking Information



- ① LLLLLLLLL: Production Batch
- ② JL701Nx: Chip Model
- ③ x: Built-in flash size
 - 0: No Flash Memory
 - 2: 2Mbit Flash
 - 4: 4Mbit Flash
 - 8: 8Mbit Flash
 - 6: 16Mbit Flash
 - 3: 32Mbit Flash



6 Solder-Reflow Condition

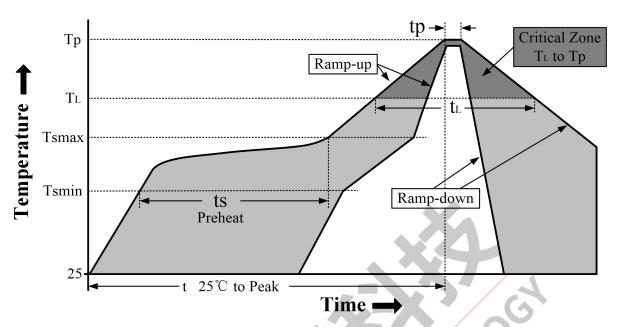


Figure 6-1 Classification Reflow Profile

Classification Profiles

Table 6-1

	Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
	Temperature Min (T _{smin})	100℃	150℃
Preheat/	Temperature Max (T _{smax})	150℃	200℃
Soak	Time (ts) from (T _{smin} to T _{smax})	60-120 seconds	60-180 seconds
Average ramp-up rate $(T_{smax}$ to $T_p)$		3℃/second max	3°C/second max
Liquidous temperature (T _L)		183℃	217℃
Time (t _L) maintained above T _L		60-150 seconds	60-150 seconds
Peak package body temperature (T _p)		See Table 6-2	See Table 6-3
Time within 5°C of actual Peak Temperature (tp) ²		10-30 seconds	20-40 seconds
Ramp-down rate (T _p to T _L)		6°C/second max	6°C/second max
Time 25℃	to peak temperature	6 minutes max	8 minutes max

Note 1: All temperatures refer to topside of the package, measured on the package body surface.

Note 2: Time within 5° C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" minimum and "user" maximum.

SnPb - Classification Temperature

Table 6-2

Package Thickness	Volume mm ³ < 350	Volume mm³ ≥ 350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5℃



Package	Volume mm ³	Volume mm ³	Volume mm ³
Thickness	< 350	350 - 2000	> 2000
< 1.6mm	260℃	260℃	260℃
1.6 mm - 2.5mm	260℃	250℃	245℃
> 2.5mm	250°C	245℃	245℃





7 Storage Condition

7.1 Moisture Sensitivity Level

JL7018F is qualified to moisture sensitivity level MSL3 in accordance with JEDEC J-STD-033.

7.2 Storage Alert

- 1. Calculated shelf life in sealed bag 12 months at < 40°C and 90% relative humidity (RH).
- 2. Peak package body temperature ≤260°C.
- 3. After bag is opened, devices that will be subjected to reflow solder or other high temperature process must be mounted within 168 hours of factory conditions ≤30°C/60%RH or stored per J-STD-033.
- 4. Devices require bake before mounting if humidity indicator card reads > 10% for level 2a-5a devices or > 60% for level 2 devices when read at 23 ± 5 °C, or 3a or 3b are not met.
 - 5. Please refer to IPC/JEDEC J-STD-033 for baking procedure if necessary.





8 Revision History

Date	Revision	Description
2022.04.09	V1.0	Initial Release
2022.06.08	V1.1	Add Block Diagram &IC Marking Information & Solder-Reflow Condition
2022.09.20	V1.2	Add Storage Condition & Update IC Marking Information
2023.02.22	V1.3	Update Pin Description

